

Title (en)
METHODS FOR ON-DIE MEMORY TERMINATION AND MEMORY DEVICES AND SYSTEMS EMPLOYING THE SAME

Title (de)
VERFAHREN FÜR SPEICHERTERMINIERUNG AUF DEM CHIP UND SPEICHERVORRICHTUNGEN UND -SYSTEME MIT VERWENDUNG DAVON

Title (fr)
PROCÉDÉS DE TERMINAISON DE MÉMOIRE SUR PUCE ET DISPOSITIFS DE MÉMOIRE ET SYSTÈMES LES UTILISANT

Publication
EP 3714457 B1 20230712 (EN)

Application
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Priority

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Abstract (en)
[origin: US2019155544A1] Methods, systems, and apparatuses related to memory operation with on-die termination (ODT) are provided. A memory device may be configured to provide ODT at a first portion (e.g., rank) during communications at a second portion (e.g., rank). For example, a memory device may receive a first command instructing a first portion to perform a first communication. The device may transmit, from the first portion, a signal instructing a second portion to enter an ODT mode. The device may perform, with the first portion, the first communication with a host while the second portion is in the ODT mode. The signal may be provided at an ODT I/O terminal of the first portion coupled to an ODT I/O terminal of the second portion.

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